

<b>Notice of References Cited</b>	Application/Control No. 10/719,083		Applicant(s)/Patent Under Reexamination HWANG ET AL.	
	Examiner Patricia A. George		Art Unit 1765	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-5,702,776	12-1997	Hayase et al.	428/1.32
*	C	US-5,959,298	09-1999	Belcher et al.	250/338.3
*	D	US-5,962,191	10-1999	Nozaki et al.	430/287.1
*	E	US-6,506,535	01-2003	Mizutani et al.	430/270.1
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	M	US-			

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#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	Meador et al.; 193-nm Multilayer Imaging Systems; Proc. SPIE ZVol. 5039, June 12, 2003; Advances in Resist Technology and Processing XX; Theodore H. Fedynyshyn, Ed.
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*	W	SPI conference proceedings; Proc. SPIE Vol. 3999, March 2000; High Performance 193-nm Positive Resist Using Alternating Polymer Systems of Functionalized Cyclic Olefins/Maleic Anhydride also published at JRS Corporation in 2002
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.